



# Bipolar NPN Bare Die – BTN6023

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## Part Description

The BTN6023 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

## Key Parameters:

- VCBO = 60V
- VCEO = 50V
- VEBO = 6V
- hFE = 120-400 @ VCE = 2V, IC = 0.5A
- VCE(Sat) = 0.35V @ IC = 1A, IB = 50mA
- fT = 280 MHz @ VCE = 2V, IE = 0A
- COBO = 12pF @ VCB = 10V

## Features

Low VCE(sat). Designed to provide performance equivalent to ROHM 2SC4672

## Die Size (Unawn)

790µm X 790µm, 31 Mils X 31 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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